IN THE U.S. PATENT AND TRADEMARK OFFICE

In re application of

Ryuji KOBAYASHI

Conf.

Application No. NEW NATIONAL PHASE

Group

Filed May 26, 2006

Examiner

SEMICONDUCTOR LASER AND METHOD OF MANUFACTURING THE SAME

INFORMATION DISCLOSURE STATEMENT (SUBMISSION CONCURRENT WITH THE FILING OF A NEW PATENT APPLICATION)

Assistant Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

May 26, 2006

Sir:

Pursuant to 37 C.F.R. §§ 1.97 and 1.98, and in fulfillment of the duty of disclosure under 37 C.F.R. § 1.56, applicant(s) hereby submit(s) an Information Disclosure Statement for consideration by the Examiner.

I. LIST OF PATENTS, PUBLICATIONS OR OTHER INFORMATION

The patents, publications, or other information submitted for consideration by the Office are listed on PTO-1449, attached hereto.

II. COPIES

- Copies of the U.S. patents or publications are not submitted since the USPTO has waived their submission for applications filed after June 30, 2003.
- Submitted herewith is a legible copy of (i) each foreign patent; (ii) each publication or that portion which caused it to be listed; and (iii) all other information or that portion which caused it to be listed.
- This application is a National Phase of a PCT application. Some or all of the documents listed on the PTO-1449 are not enclosed because they were cited in the International Search Report and copies should have been forwarded from the International Search Authority pursuant to the trilateral agreement between the USPTO, EPO and JPO, or they are U.S. patents or U.S. published applications. If copies are needed, please contact the undersigned.

Docket No. 8028-1060

III. CONCISE EXPLANATION OF THE RELEVANCE APORT OF THE RELEVANCE APO (check at least one box)

DOCUMENTS IN THE ENGLISH LANGUAGE \boxtimes a.

The attached non U.S. patents, non U.S. patent application publications, foreign publications, or other information in the English language do not require a statement of relevancy.

DOCUMENTS NOT IN THE ENGLISH LANGUAGE b. \boxtimes

A concise explanation of the relevance of all patents, publications, or other information listed that is not in the English language is as follows:

Cited in the specification

冈 FOREIGN SEARCH REPORT OR ACTION c.

> An English language version of the search report or action that indicates the degree of relevance found by the foreign office is attached, thereby for satisfying the requirement a explanation. See MPEP 609(A)(3).

OTHER \Box d.

The following additional information is provided for the Examiner's consideration.

FEES

This Information Disclosure Statement is being filed concurrently with the filing of a new patent application; therefore, no fee is required.

If The Examiner has any questions concerning this IDS, he/she is requested to contact the undersigned.

Respectfully submitted,

YOUNG & THOMPSON

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BC/ia

Form PTO-1449(s) Enclosures: 冈

> \boxtimes Documents

Foreign Search Report X

Other: • FTO-1449

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION					Attorney Docket No.: 8028-1160		Application No.: NEW NATIONAL PHASE				
					Applicant: Ryuji KOBAYASHI						
(Use several sheets if necessary)					Filing Date: May 26, 2006		Group Art Unit:				
-		Ĺ	J.S. PATE	ENT	DOCUMENTS						
Examiner Document Number			Date	Name		Class	s S	Subclass	Filing date (if appropriate)		
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EXAMINER:				[DATE CONSIDERED						

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

* English language abstract provided for the Examiner's convenience